

IN THE CLAIMS

1-16. (canceled).

17. (currently amended) A method of fabrication of a semiconductor device, comprising the steps of:

die bonding of a plurality of semiconductor chips on a substrate;

forming of ~~an a single-layer~~ insulation film on said substrate, wherein a top surface and at least a portion of side surfaces of said plurality of semiconductor chips are is incrustated in said insulation film;

forming of a connection hole reaching a semiconductor chip of said plurality of semiconductor chips on said insulation film; and

forming of wiring on said insulation film, wherein said wiring is connected to said semiconductor chip through said connection hole.

18. (original) The method of fabrication of a semiconductor device according to claim 17, further comprising the steps of:

forming of an upper layer insulation film on said insulation film, wherein said upper layer insulation film covers said wiring;

forming of a connection hole reaching said wiring, on said upper layer insulation film; and

forming of an electrode on said upper layer insulation film, wherein said electrode is connected to said wiring through said connection hole.

19. (currently amended) The method of fabrication of a semiconductor device according to claim 17, wherein said substrate is a silicon semiconductor wafer.

20. (original) The method of fabrication of a semiconductor device according to claim 17, wherein

said die bonding of said plurality of semiconductor chips on said substrate comprises die bonding of each said semiconductor chips on said substrate, wherein each said semiconductor chip is set so as to float on an adhesive resin applied on said substrate.

21. (original) The method of fabrication of a semiconductor device according to claim

17, wherein

after said step of forming said wiring, said substrate is removed from said semiconductor chip and said insulation film.